# **SEMICONDUCTOR**

### **4.0A GLASS PASSIVATED BRIDGE RECTIFIER**

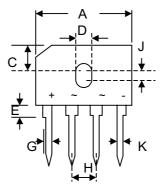
## Data Sheet 1333 Rev.A

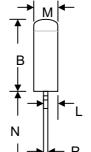
### **Features**

- Glass Passivated Die Construction
- Low Forward Voltage Drop
- High Current Capability
- High Reliability
- High Surge Current Capability
- Ideal for Printed Circuit Boards
- UL Recognized File # E223064

### **Mechanical Data**

- Case: Molded Plastic
- Terminals: Plated Leads Solderable per MIL-STD-202, Method 208
- Polarity: As Marked on Body
- Weight: 4.0 grams (approx.)
- Mounting Position: Any
- Marking: Type Number





GBU									
Dim	Min	Max	Min	Max					
Α	21.8	22.3	0.858	0.878					
В	18.30	18.80	0.720	0.740					
С	7.40	7.90	0.291	0.311					
D	3.50	4.10	0.138	0.161					
Е	1.52	2.03	0.060	0.080					
G	2.16	2.54	0.085	0.1					
Н	4.83	5.33	0.190	0.210					
J	1.65	2.16	0.065	0.085					
K	1.65	2.03	0.065	0.080					
L	0.76	1.02	0.030	0.040					
M	3.30	3.56	0.130	0.140					
N	17.50	18.00	0.689	0.709					
Р	0.46	0.56	0.018	0.022					
	In mm		In inch						

## Maximum Ratings and Electrical Characteristics @TA=25°C unless otherwise specified

Single Phase, half wave, 60Hz, resistive or inductive load. For capacitive load, derate current by 20%.

Characteristic	Symbol	GBU4A	GBU4B	GBU4D	GBU4G	GBU4J	GBU4K	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	VRRM VRWM VR	50	100	200	400	600	800	V
RMS Reverse Voltage	VR(RMS)	35	70	140	280	420	560	٧
Average Rectified Output Current @T <sub>C</sub> = 100°C @T <sub>A</sub> = 40°C	lo	4.0 3.0						Α
Non-Repetitive Peak Forward Surge Current 8.3ms Single half sine-wave superimposed on rated load (JEDEC Method)	IFSM	150						А
I <sup>2</sup> t Rating for Fusing (t < 8.35ms)	I <sup>2</sup> t	93						A <sup>2</sup> s
Forward Voltage (per element) @I <sub>F</sub> = 4.0A	VFM	1.0						V
Peak Reverse Current @T <sub>A</sub> = 25°C At Rated DC Blocking Voltage @T <sub>C</sub> = 100°C	) IR	5.0 500						μA
Typical Thermal Resistance (per leg) (Note 1)	$R_{ heta}$ JA	19						K/W
Typical Thermal Resistance (per leg) (Note 2)	RθJC	4.0						K/W
Operating and Storage Temperature Range	Tj, Tstg	-55 to +150						°C

Note: 1. Thermal resistance junction to ambient, mounted on PCB at 9.5mm lead length with 12mm<sup>2</sup> copper pads.

2. Thermal resistance junction to case, mounted on 5.0 x 4.0 x 0.8cm thick AL plate.

- 221 West Industry Court Deer Park, NY 11729-4681 (631) 586-7600 FAX (631) 242-9798
  - World Wide Web Site http://www.sensitron.com E-Mail Address sales@sensitron.com •

I<sub>FSM</sub>, PEAK FORWARD SURGE CURRENT (A)

160

120

40

0

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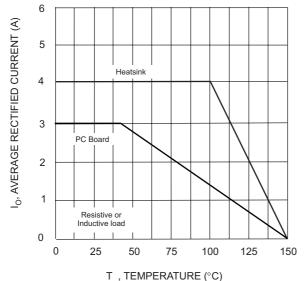
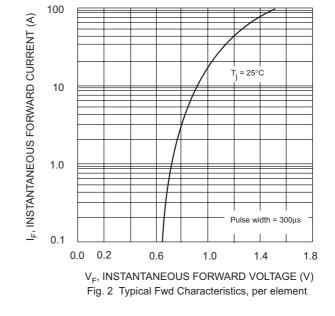


Fig. 1 Forward Current Derating Curve



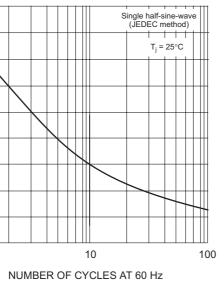
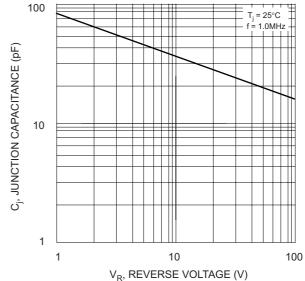


Fig. 3 Maximum Non-Repetitive Surge Current





#### **TECHNICAL DATA**

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